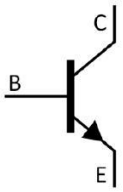
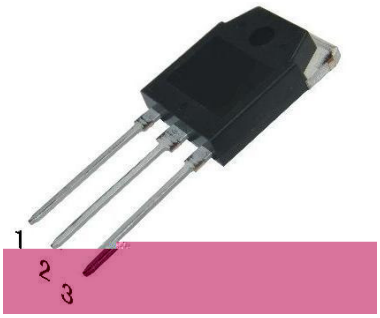
Silicon NPN transistor in a TO-3P Plastic Package.

High breakdown voltage, high speed, wide SOA.

Horizontal deflection output for TV and CRT monitor.





PIN1 Base PIN 2 Collector PIN 3 Emitter

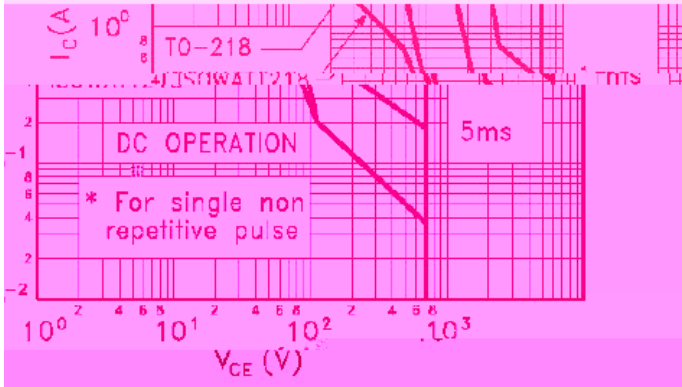
See Marking Instructions.

Rev.D Mar.-2016

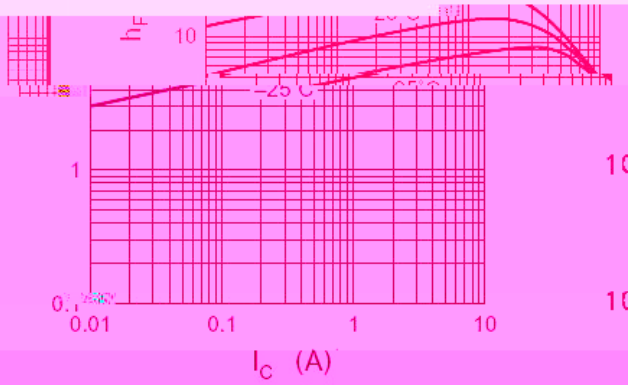
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage	V_{CES}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	20	A
Peak Collector Current	I_{CP}	30	A
Base Current	P_C	3	W
Collector Power Dissipation	$P_{C(TC=25\ )}$	200	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=1mA I_E=0	1500			V
Collector to Base Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	800			V
Collector to Emitter Breakdown Voltage	V_{EBO}	I_E=1mA I_C=0	6			V

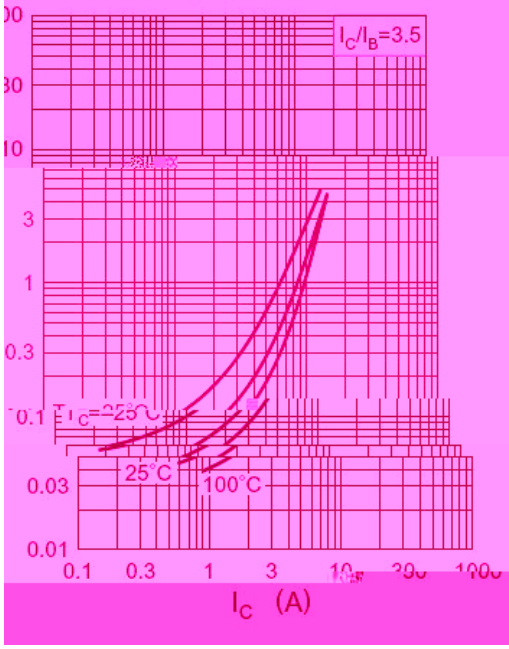
SOA



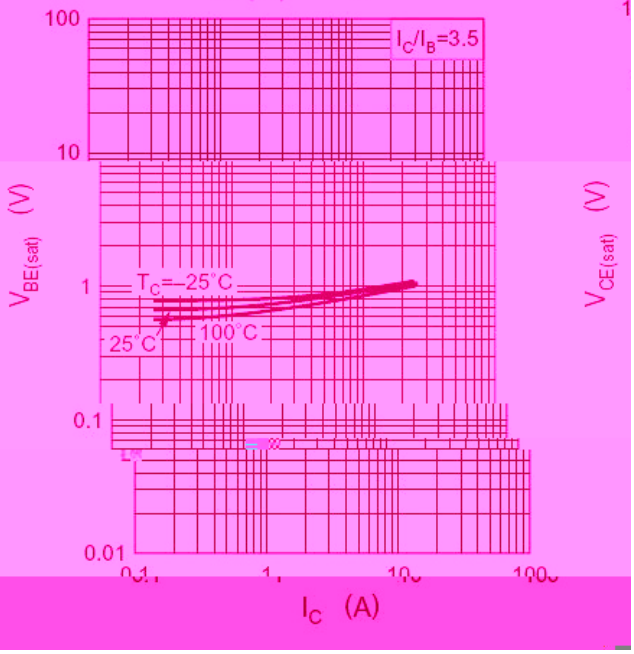
h_{FE} — I_C

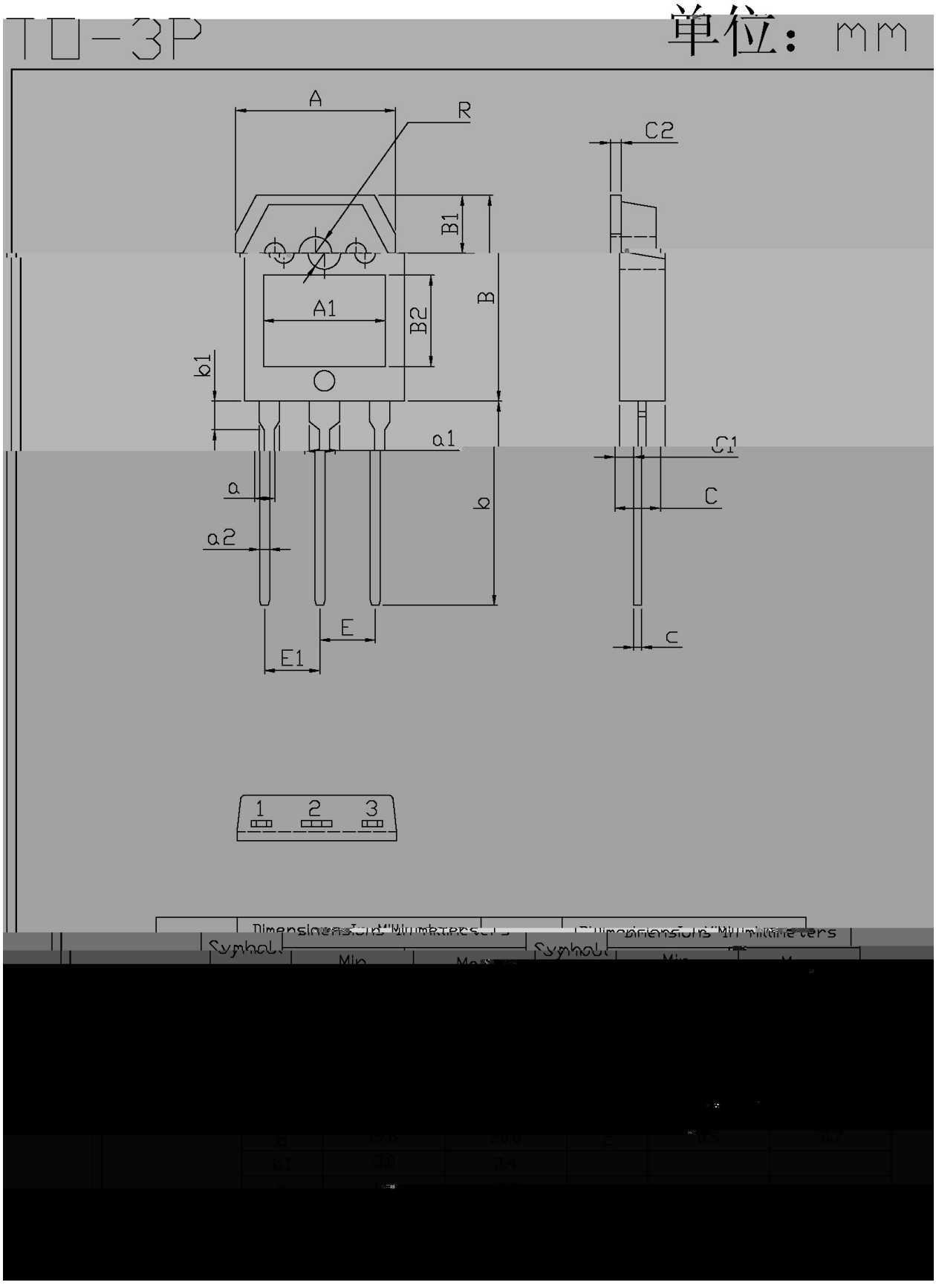


$V_{CE(sat)}$ — I_C



$V_{BE(sat)}$ — I_C




TO-3P
单位：mm
A
R
C2
B1
A1
B2
B
b1
a1
C1
a
b
C
a2
E
E1
c
1 2 3

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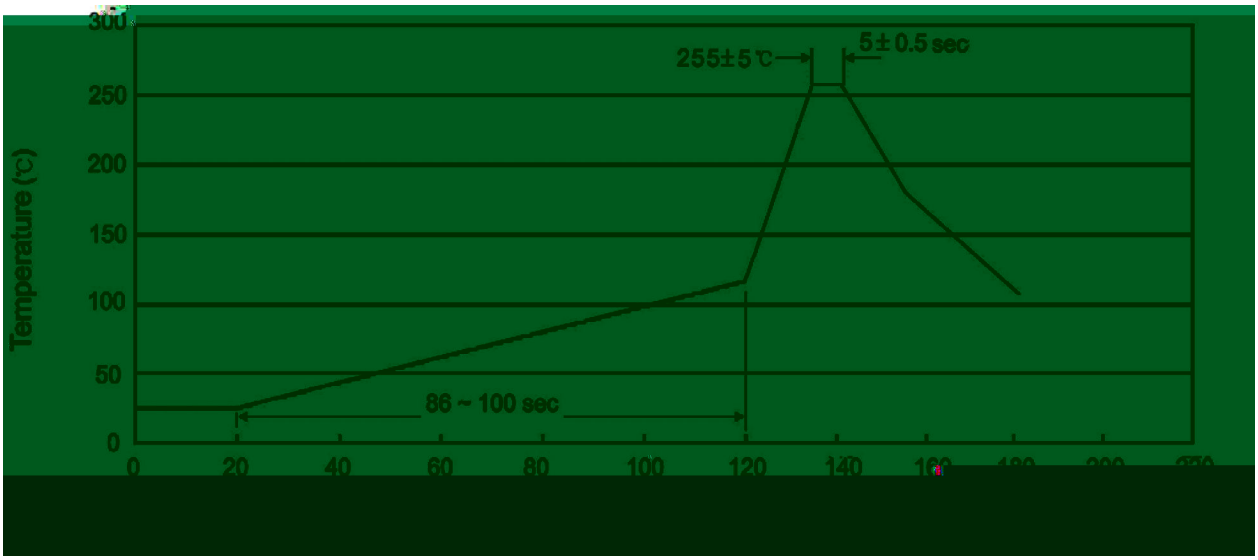

			Note:
1	25 150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255 5	5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3		2 10 /sec.	3. Cooling Speed: 2~10 /sec.

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-3P	30	15	450	5	2250	497.5×46×8	555×164×50	575 290 180